Excellent Integrated System Limited

Stocking Distributor

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ON Semiconductor NUP412VP5T5G

For any questions, you can email us directly: sales@integrated-circuit.com

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NUP412VP5

Low Capacitance Quad Array for ESD Protection

This integrated transient voltage suppressor device (TVS) is designed for applications requiring transient overvoltage protection. It is intended to be used in sensitive equipment such as wireless headsets, PDAs, digital cameras, computers, printers, communication systems, and other applications. The integrated design provides very effective and reliable protection for four separate lines using only one package. This device is ideal for situations where board space is at a premium.

Features

- ESD Protection: IEC61000-4-2: Level 4
- Four Separate Unidirectional Configurations for Protection
- Low Leakage Current < 1 μA @ 9 V
- Small SOT-953 SMT Package
- Low Capacitance
- These are Pb-Free Devices

Benefits

- Provides Protection for ESD Industry Standards: IEC 61000, HBM
- Protects Four Lines Against Transient Voltage Conditions
- Minimize Power Consumption of the System
- Minimize PCB Board Space

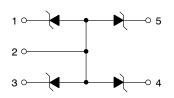
Typical Applications

- Cellular and Portable Electronics
- Serial and Parallel Ports
- Microprocessor Based Equipment
- Notebooks, Desktops, Servers



ON Semiconductor®

http://onsemi.com





SOT-953 CASE 526AB

MARKING DIAGRAM



2 = Specific Device CodeM = Date & Assembly Code

ORDERING INFORMATION

Device	Device Package Shipping			
NUP412VP5T5G	SOT-953 (Pb-Free)	8000 / Tape & Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Distributor of ON Semiconductor: Excellent Integrated System Limited

Datasheet of NUP412VP5T5G - TVS DIODE 9VWM SOT953

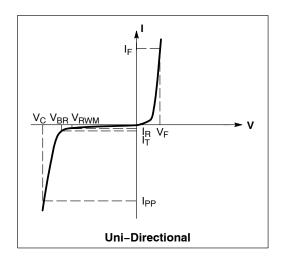
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NUP412VP5

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V_{BR}	Breakdown Voltage @ I _T
I _T	Test Current
ΘV _{BR}	Maximum Temperature Coefficient of V _{BR}
IF	Forward Current
V _F	Forward Voltage @ I _F
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}
I _{ZK}	Reverse Current
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}



MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Peak Power Dissipation (8 X 20 μs @ T _A = 25°C) (Note 1)	P _{PK}	18	W
Thermal Resistance Junction-to-Ambient Above 25°C, Derate	$R_{ hetaJA}$	560 4.5	°C/W mW/°C
Maximum Junction Temperature	T _{Jmax}	150	°C
Operating Junction and Storage Temperature Range	T _J T _{stg}	-55 to +150	°C
Lead Solder Temperature (10 seconds duration)	TL	260	°C
Human Body Model (HBM) Machine Model (MM)	ESD	8000 400	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ELECTRICAL CHARACTERISTICS $(T_A = 25^{\circ}C)$

	Device	Breakdown Voltage V _{BR} @ 5 mA (Volts)		Leakage Current I _{RM} @ V _{RM}		Typ Capacitance @ 0 V Bias (pF) (Note 2)		Typ Capacitance @ 3 V Bias (pF) (Note 2)		
Device	Marking	Min	Nom	Max	V _{RWM}	I _{RWM} (μA)	Тур	Max	Тур	Max
NUP412VP5 (Note 3)	2	11.4	12	12.7	9.0	0.5	6.5	10	3.5	5.0

Capacitance of one diode at f = 1 MHz, T_A = 25°C.
 V_{BR} at 5 mA.

^{1.} Non-repetitive current.



NUP412VP5

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TYPICAL ELECTRICAL CHARACTERISTICS

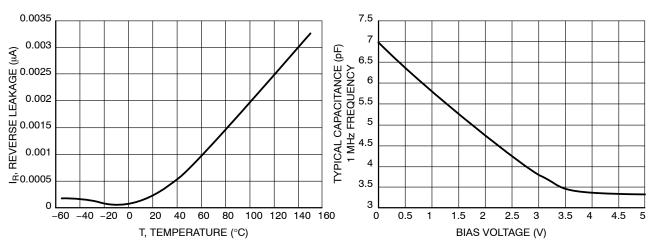


Figure 1. Reverse Leakage versus Temperature

Figure 2. Capacitance

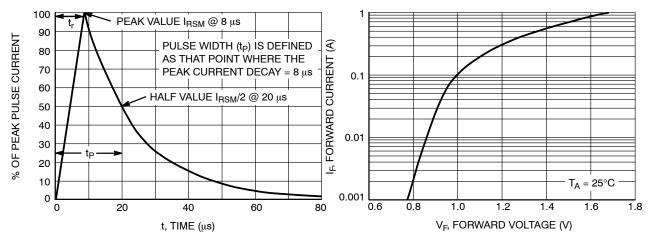


Figure 3. 8 \times 20 μs Pulse Waveform

Figure 4. Forward Voltage

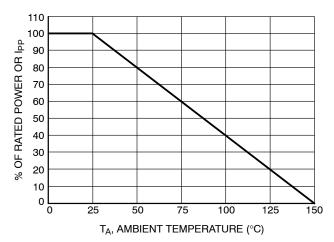


Figure 5. Power Derating Curve



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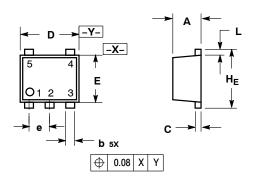
Datasheet of NUP412VP5T5G - TVS DIODE 9VWM SOT953

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NUP412VP5

PACKAGE DIMENSIONS

SOT-953 CASE 527AB-01 **ISSUE B**



NOTES:

- NOTES:

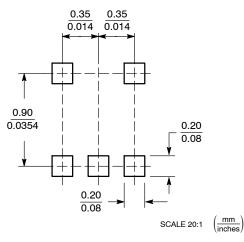
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETERS

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.34	0.42	0.50	0.013	0.017	0.020
b	0.10	0.15	0.20	0.004	0.006	0.008
С	0.05	0.10	0.15	0.002	0.004	0.006
D	0.95	1.00	1.05	0.037	0.039	0.041
Е	0.75	0.80	0.85	0.03	0.032	0.034
е	0.35 BSC				0.014 BS	C
L	0.05	0.10	0.15	0.002	0.004	0.006
HE	0.95	1.00	1.05	0.037	0.039	0.041

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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